

## Supporting Information

### All-Textile Triboelectric Sensor for Wearable Teleoperated Human-Machine Interaction

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Table S1. Performances compare of textile pressure sensors

Working mechanism	Sensitivity	Detection limit	Range	References
resistance	14.4 kPa <sup>-1</sup>	2 Pa	2~2800 Pa	1
resistance	0.358 mA kPa <sup>-1</sup>	-	<60 kPa	2
resistance	1.03 kPa <sup>-1</sup>	20 mg	<10 kPa	3
capacitance	0.21 kPa <sup>-1</sup>	-	<3.9 MPa	4
resistance	0.012 kPa <sup>-1</sup>	1.27 kPa	1.27<254 kPa	5
piezoelectric	1.1 V kPa <sup>-1</sup>	0.1 Pa	-	6
resistance	18.376 kPa <sup>-1</sup>	2 Pa	0.002~10 kPa	7
triboelectric	6.23 mV kPa <sup>-1</sup>	362 Pa	0.362 ~ 326 kPa	8
triboelectric	-	0.98 N	0.98 ~147 N	9
triboelectric	0.77V Pa <sup>-1</sup>	-	<14 kPa	10
triboelectric	0.385V kPa <sup>-1</sup>	2.6 kPa	2.6~400 kPa	11
triboelectric	1.1 V kPa <sup>-1</sup>	100 Pa	0.1~400 kPa	This work

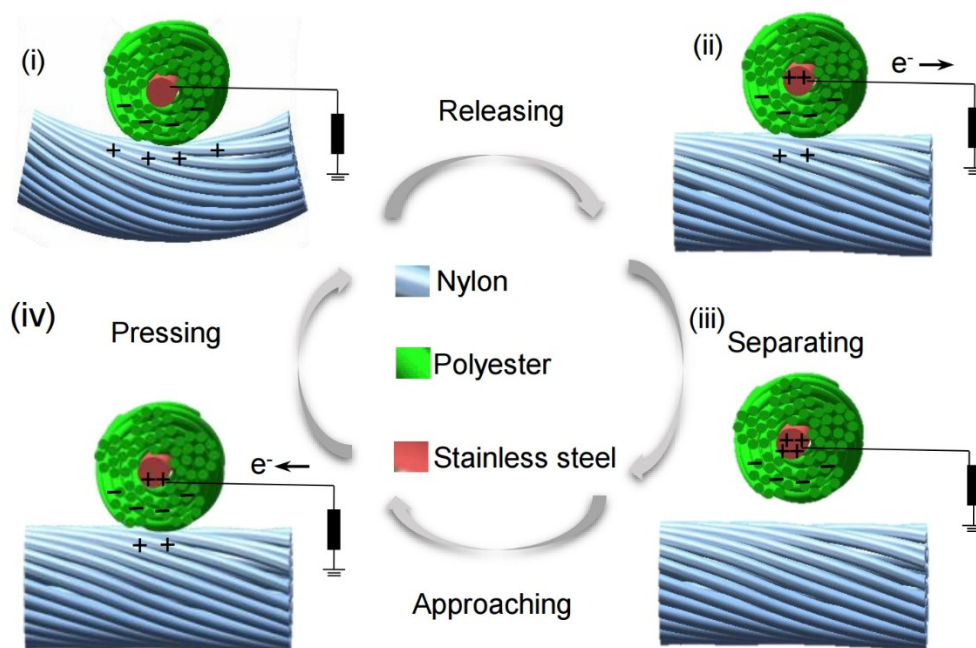
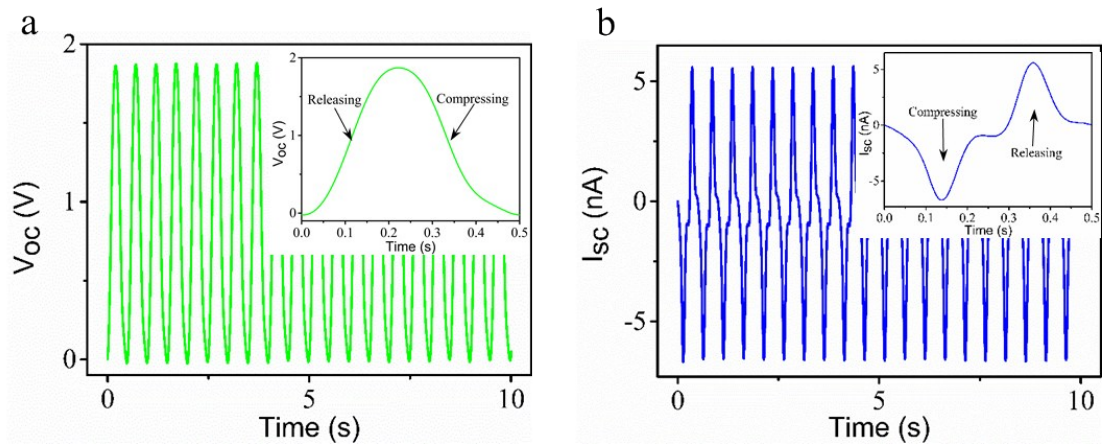
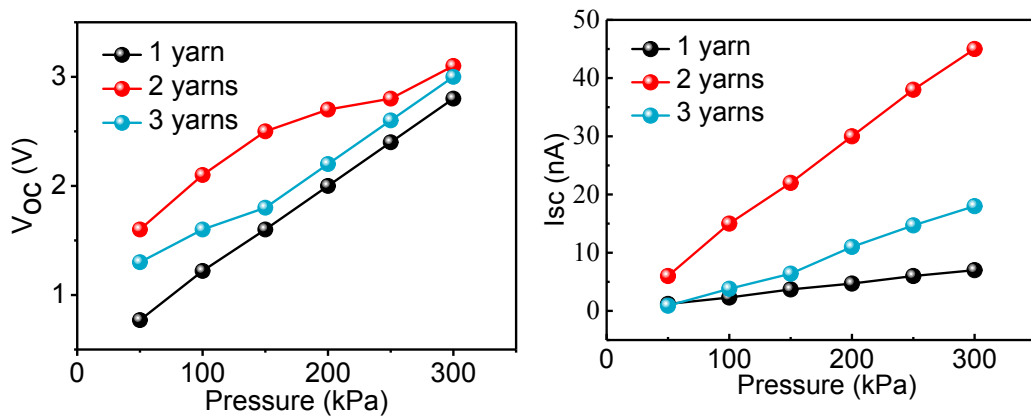


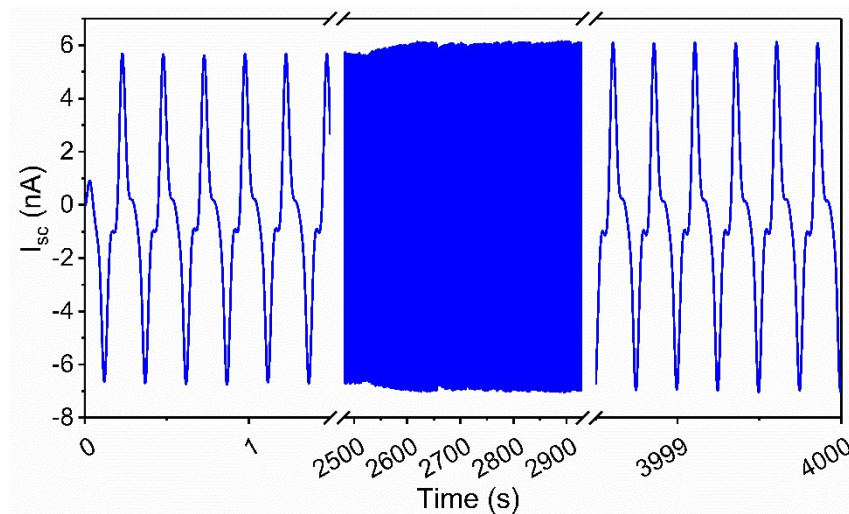
Figure S1. The working mechanism of the ATTS



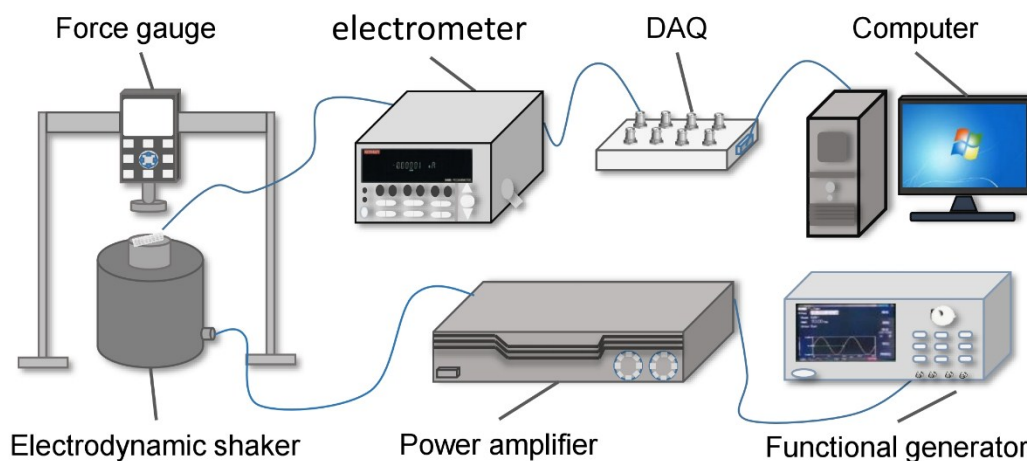
**Figure S2.** The open-circuit voltage (a) and the short-circuit current (b) under applied forces of 20 N at 2 Hz



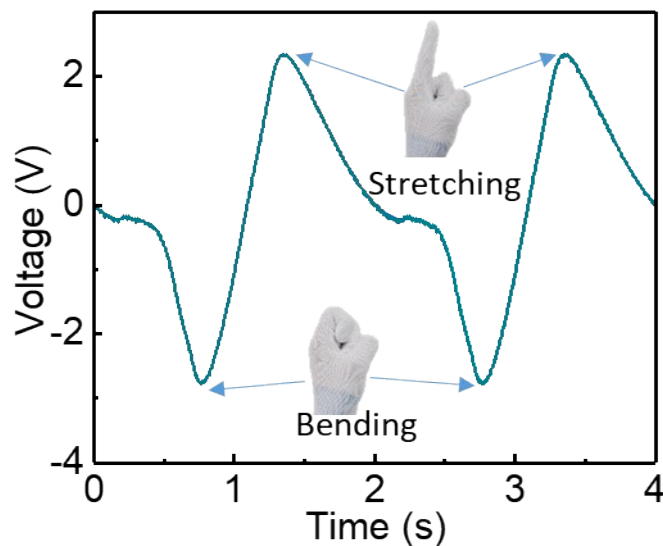
**Figure S3.** The open-circuit voltages (a) the short-circuit current (b) in the pressure region from 50 kPa to 300 kPa for three ATTSs sewn with different numbers of sensing yarns



**Figure S4.** The mechanical durability characterization of the ATTS under an applied force (20 N, 4 Hz) for 16000 cycles.



**Figure S5.** Experimental setup to analyze the electrical output performance of the ATTS



**Figure S6.** The output voltage of the ATTS-integrated glove during two cycles of the finger bending and stretching process. Negative voltages obtained in bending cycles while positive voltages obtained in stretching cycles, demonstrating the polarity of the output voltage in the bending and stretching process.

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